



100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} max | I _D max T _C = +25°C |
|----------------------|------------------------------|--|
| 100V | $28m\Omega$ @ $V_{GS} = 10V$ | 55A |

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_a Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

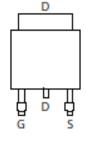
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Mechanical Data

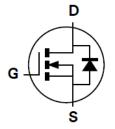
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

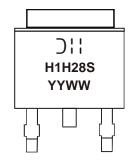
Ordering Information (Note 5)

| Part Number | Case | Packaging |
|-------------------|-------|-------------------|
| DMNH10H028SK3Q-13 | TO252 | 2,500/Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- $5. \ For packaging \ details, go \ to \ our \ website \ at \ http://www.diodes.com/products/packages.html.$

Marking Information



Oll = Manufacturer's Marking
H1H28S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 15 = 2015)
WW = Week Code (01 to 53)



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

| Characteristic | | Symbol | Value | Unit |
|--|---|------------------|----------|------|
| Drain-Source Voltage | | V _{DSS} | 100 | V |
| Gate-Source Voltage | | V_{GSS} | ±20 | V |
| Continuous Drain Current, V _{GS} = 10V | $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$ | I _D | 55 39 | А |
| Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) | I _{DM} | 58 | Α | |
| Maximum Continuous Body Diode Forward Current (Note 6) | | I _S | 2.2 | Α |
| Avalanche Current, L = 0.1mH | | I _{AS} | 29 | Α |
| Avalanche Energy, L = 0.1mH | | Eas | 43 | mJ |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|---|-----------------------------------|-----------------|------|------|
| Total Power Dissipation (Note 6) | P _D | 2.0 | W | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | 6 | 74 | °C/W |
| Thermal Resistance, Suriction to Ambient (Note o) | t<10s | $R_{	heta JA}$ | 25 | |
| Total Power Dissipation (Note 7) | P_{D} | 3.7 | W | |
| Thermal Resistance, Junction to Ambient (Note 7) | Steady State | | 40 | |
| Thermal Resistance, Junction to Ambient (Note 7) | t<10s | $R_{\theta JA}$ | 13 | °C/W |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.2 | | |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +175 | °C | |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| - | | | | | | | |
|---|---------------------|-----|-------|------|------|---|--|
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
| OFF CHARACTERISTICS (Note 8) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 100 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current, T _J = +25°C | I _{DSS} | 1 | _ | 1 | μΑ | $V_{DS} = 100V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 8) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 2.0 | 2.5 | 4.0 | V | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 20 | 28 | mΩ | $V_{GS} = 10V, I_D = 20A$ | |
| Diode Forward Voltage | V_{SD} | _ | 0.7 | 1.2 | V | $V_{GS} = 0V, I_{S} = 1.0A$ | |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | | |
| Input Capacitance | C _{iss} | _ | 2,245 | _ | pF | V _{DS} = 50V, V _{GS} = 0V, f = 1MHz | |
| Output Capacitance | Coss | _ | 173 | _ | pF | | |
| Reverse Transfer Capacitance | C _{rss} | _ | 68 | _ | pF | | |
| Gate Resistance | R_g | _ | 1.9 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge (V _{GS} = 10V) | Q_g | _ | 36 | _ | nC | | |
| Total Gate Charge (V _{GS} = 6V) | Q_g | _ | 22 | _ | nC | \/ = 50\/ - = 30 \ | |
| Gate-Source Charge | Q_{gs} | _ | 7.3 | _ | nC | $-V_{DS} = 50V, I_{D} = 20A$ | |
| Gate-Drain Charge | Q_{gd} | _ | 9.2 | _ | nC | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 6.4 | _ | ns | $V_{GS} = 10V, V_{DS} = 50V,$ $R_G = 3\Omega, I_D = 20A$ | |
| Turn-On Rise Time | t _R | _ | 5.8 | _ | ns | | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 17.8 | _ | ns | | |
| Turn-Off Fall Time | t _F | _ | 4.8 | _ | ns | | |
| Body Diode Reverse Recovery Time | t _{RR} | _ | 35 | _ | ns | $I_F = 20A$, $di/dt = 100A/\mu s$ | |
| Body Diode Reverse Recovery Charge | Q _{RR} | | 47 | _ | nC | $I_F = 20A$, $di/dt = 100A/\mu s$ | |

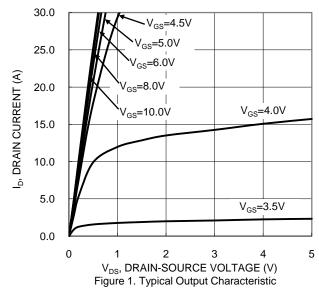
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing. Notes:





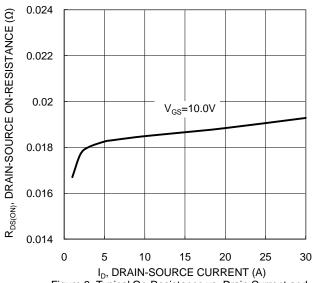


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

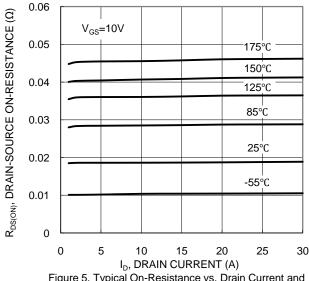
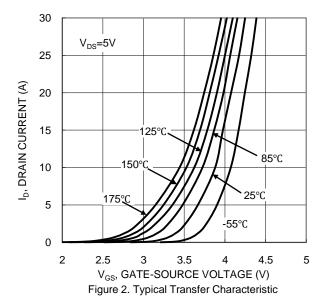
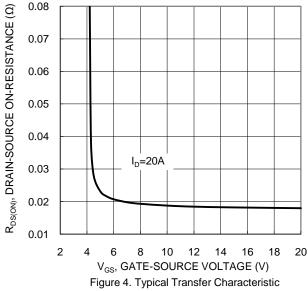


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





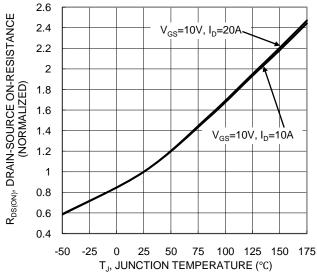


Figure 6. On-Resistance Variation with Temperature



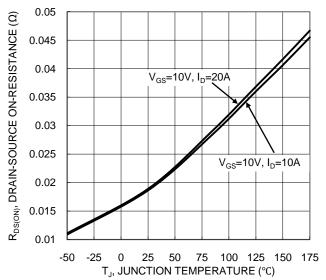
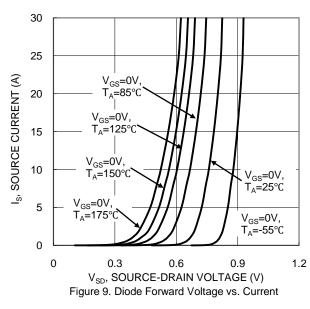
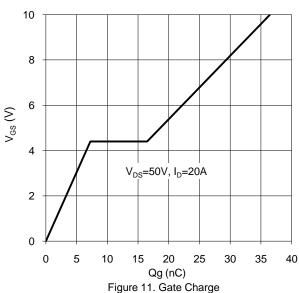
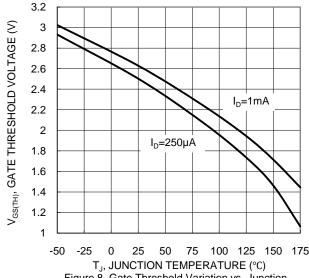


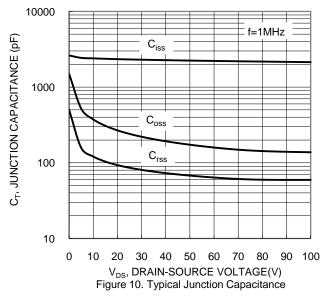
Figure 7. On-Resistance Variation with Temperature

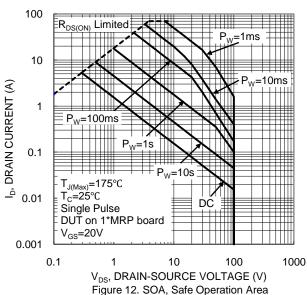




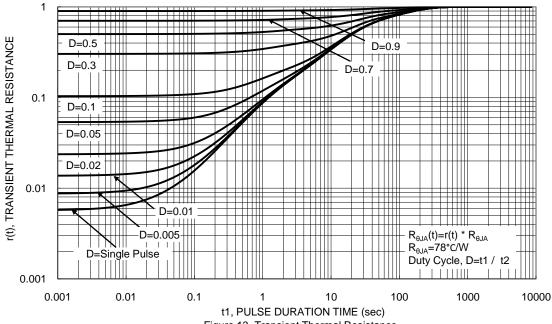


T_J, JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. Junction Temperature





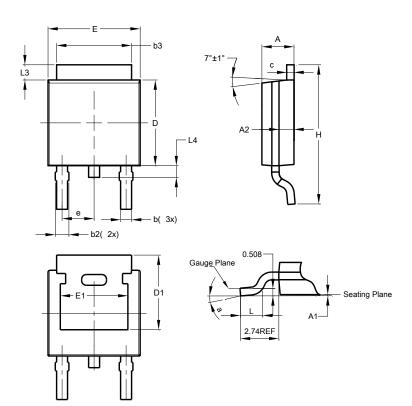






Package Outline Dimensions

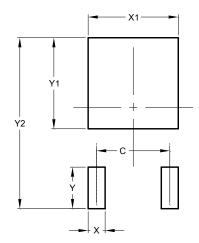
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| TO252 (DPAK) | | | | | |
|----------------------|------|-------|-------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 2.19 | 2.39 | 2.29 | | |
| A1 | 0.00 | 0.13 | 0.08 | | |
| A2 | 0.97 | 1.17 | 1.07 | | |
| b | 0.64 | 0.88 | 0.783 | | |
| b2 | 0.76 | 1.14 | 0.95 | | |
| b3 | 5.21 | 5.46 | 5.33 | | |
| С | 0.45 | 0.58 | 0.531 | | |
| D | 6.00 | 6.20 | 6.10 | | |
| D1 | 5.21 | - | - | | |
| е | - | - | 2.286 | | |
| Ε | 6.45 | 6.70 | 6.58 | | |
| E1 | 4.32 | - | - | | |
| Н | 9.40 | 10.41 | 9.91 | | |
| L | 1.40 | 1.78 | 1.59 | | |
| L3 | 0.88 | 1.27 | 1.08 | | |
| L4 | 0.64 | 1.02 | 0.83 | | |
| а | 0° | 10° | - | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

 $Please see AP02001 \ at \ http://www.diodes.com/datasheets/ap02001.pdf \ for \ the \ latest \ version.$



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 4.572 | | |
| Х | 1.060 | | |
| X1 | 5.632 | | |
| Y | 2.600 | | |
| Y1 | 5.700 | | |
| Y2 | 10.700 | | |



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